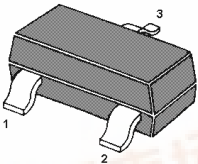


PNP Silicon Epitaxial Planar Transistor

The transistor is subdivided into three groups Q, R and S according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.

SOT-23

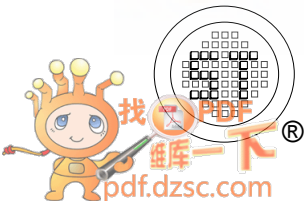


1.BASE 2.EMITTER 3.COLLECTOR

SOT-23 Plastic Package

Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	-V <sub>CBO</sub>	60	V
Collector Current	-I <sub>C</sub>	150	mA
Power Dissipation	P <sub>tot</sub>	200	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>S</sub>	-55 to +150	°C



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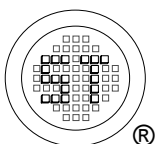
Dated : 20/10/2005

# MMBTSA1037

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## Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE}=6\text{V}$ , $-I_C=1\text{mA}$	Q $h_{FE}$ R $h_{FE}$ S $h_{FE}$	120 180 270	270 390 560	- - -
Collector Cutoff Current at $-V_{CB}=60\text{V}$	$-I_{CBO}$	-	0.1	$\mu\text{A}$
Emitter Cutoff Current at $-V_{EB}=6\text{V}$	$-I_{EBO}$	-	0.1	$\mu\text{A}$
Collector Saturation Voltage at $-I_C=50\text{mA}$ , $-I_B=5\text{mA}$	$-V_{CE(sat)}$	-	0.5	V
Collector Base Breakdown Voltage at $-I_C=50\mu\text{A}$	$-V_{(BR)CBO}$	60	-	V
Collector Emitter Breakdown Voltage at $-I_C=1\text{mA}$	$-V_{(BR)CEO}$	50	-	V
Emitter Base Breakdown Voltage at $-I_E=50\mu\text{A}$	$-V_{(BR)EBO}$	6	-	V
Transition Frequency at $-V_{CE}=12\text{V}$ , $-I_C=2\text{mA}$ , $f=30\text{MHz}$	$f_T$	120	-	MHz



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ISO/TS 16949 : 2002  
Certificate No. 05103



ISO 14001:2004  
Certificate No. 7116



ISO 9001:2000  
Certificate No. 0506098

Dated : 20/10/2005